

# FQP8N90C/FQPF8N90C

## 900V N-Channel MOSFET

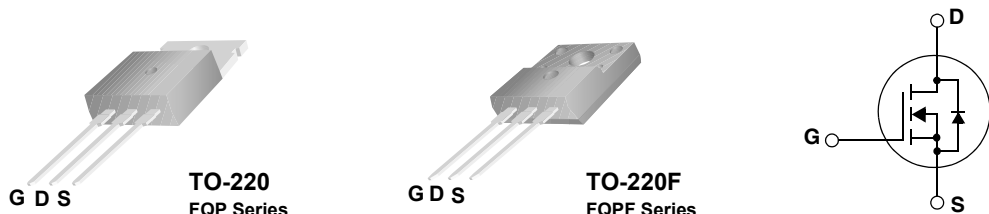
### General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supplies.

### Features

- 6.3A, 900V,  $R_{DS(on)} = 1.9\Omega @ V_{GS} = 10V$
- Low gate charge ( typical 35 nC)
- Low  $C_{rss}$  ( typical 12 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQP8N90C	FQPF8N90C	Units
$V_{DSS}$	Drain-Source Voltage	900		V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) - Continuous ( $T_C = 100^\circ\text{C}$ )	6.3	6.3 *	A
		3.8	3.8 *	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	25	25 *	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$		V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	850		mJ
$I_{AR}$	Avalanche Current (Note 1)	6.3		A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	17.1		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0		V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ ) - Derate above $25^\circ\text{C}$	171	60	W
		1.37	0.48	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		$^\circ\text{C}$

\* Drain current limited by maximum junction temperature.

### Thermal Characteristics

Symbol	Parameter	FQP8N90C	FQPF8N90C	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.73	2.08	$^\circ\text{C}/\text{W}$
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	$^\circ\text{C}/\text{W}$

## Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	900	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.95	--	V/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 900\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	$\mu\text{A}$
		$V_{DS} = 720\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 3.15\text{ A}$	--	1.6	1.9	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 3.15\text{ A}$ (Note 4)	--	5.5	--	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1600	2080	pF
$C_{oss}$	Output Capacitance		--	130	170	pF
$C_{rss}$	Reverse Transfer Capacitance		--	12	15	pF

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 450\text{ V}, I_D = 8\text{ A},$ $R_G = 25\ \Omega$	--	40	90	ns
$t_r$	Turn-On Rise Time		--	110	230	ns
$t_{d(off)}$	Turn-Off Delay Time		--	70	150	ns
$t_f$	Turn-Off Fall Time		(Note 4, 5)	--	70	150
$Q_g$	Total Gate Charge	$V_{DS} = 720\text{ V}, I_D = 8\text{ A},$ $V_{GS} = 10\text{ V}$	--	35	45	nC
$Q_{gs}$	Gate-Source Charge		--	10	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4, 5)	--	14	--

### Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	6.3	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	25	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 6.3\text{ A}$	--	--	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 8\text{ A},$	--	530	--	ns
$Q_{rr}$	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	5.8	--	$\mu\text{C}$

#### Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 40\text{ mH}, I_{AS} = 6.3\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 8\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\ \mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

## Typical Characteristics

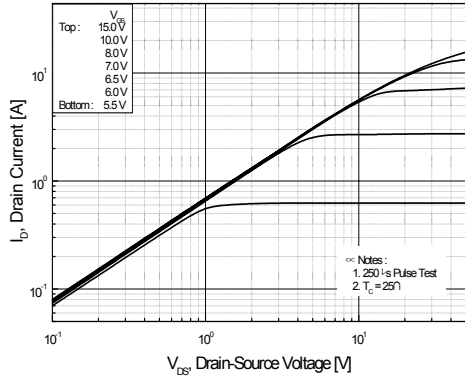


Figure 1. On-Region Characteristics

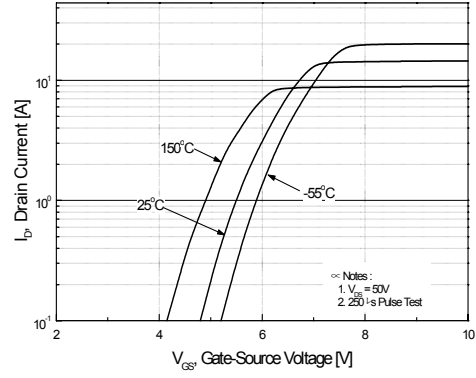


Figure 2. Transfer Characteristics

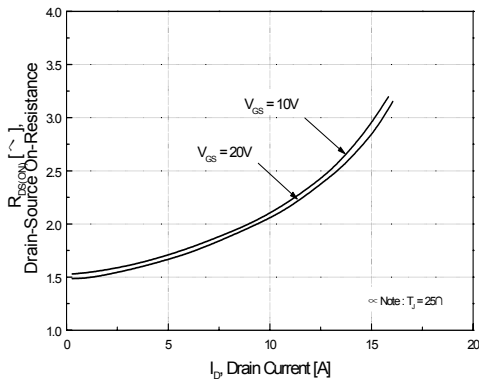


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

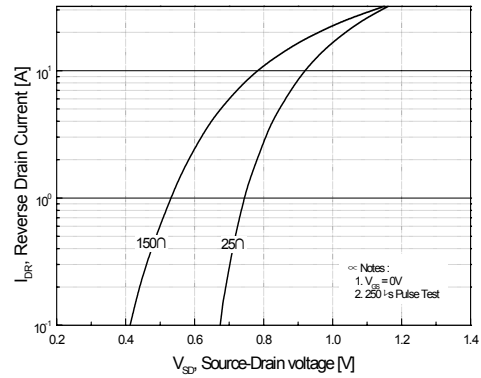


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

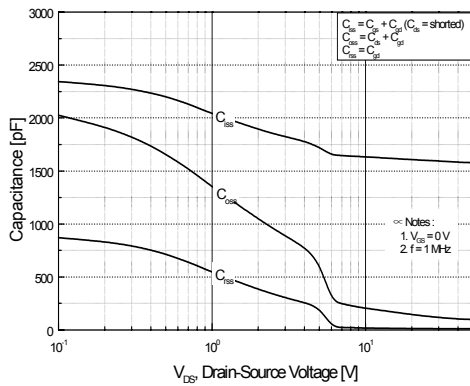


Figure 5. Capacitance Characteristics

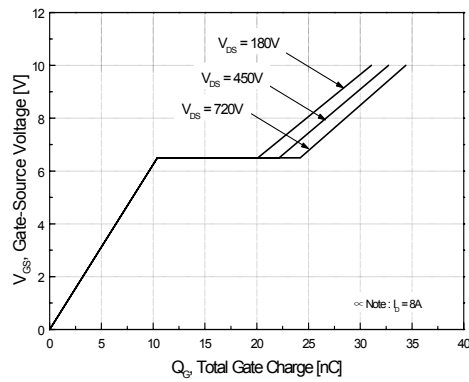
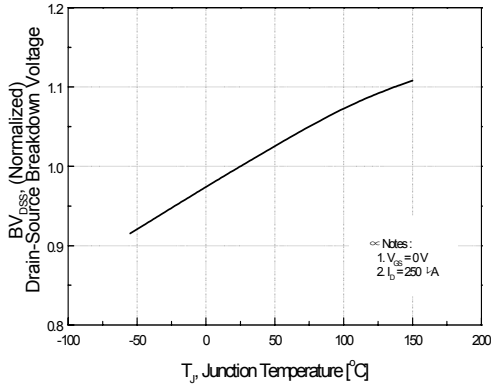
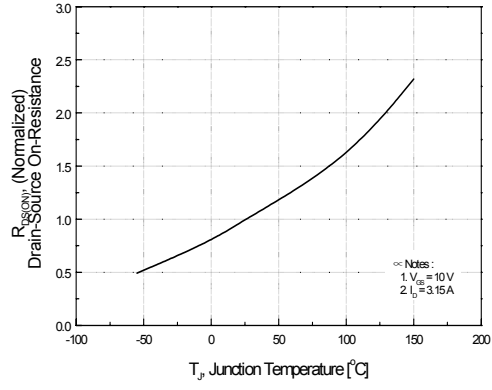


Figure 6. Gate Charge Characteristics

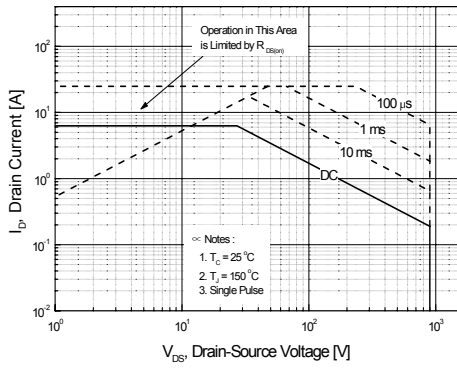
**Typical Characteristics** (Continued)



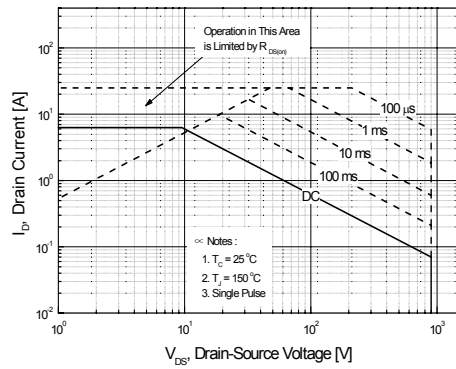
**Figure 7. Breakdown Voltage Variation vs Temperature**



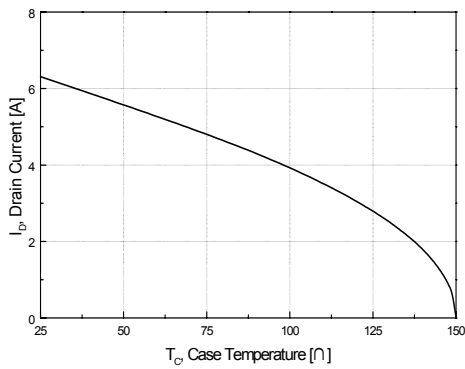
**Figure 8. On-Resistance Variation vs Temperature**



**Figure 9-1. Maximum Safe Operating Area for FQP8N90C**



**Figure 9-2. Maximum Safe Operating Area for FQPF8N90C**



**Figure 10. Maximum Drain Current vs Case Temperature**

Typical Characteristics (Continued)

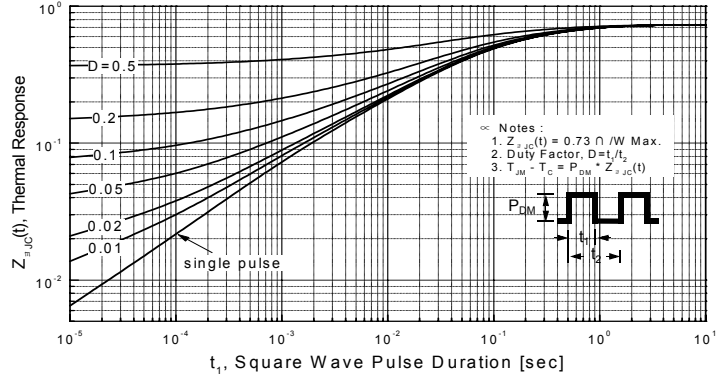


Figure 11-1. Transient Thermal Response Curve for FQP8N90C

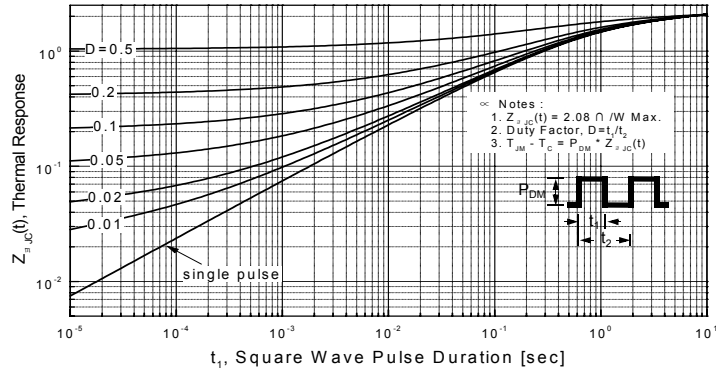
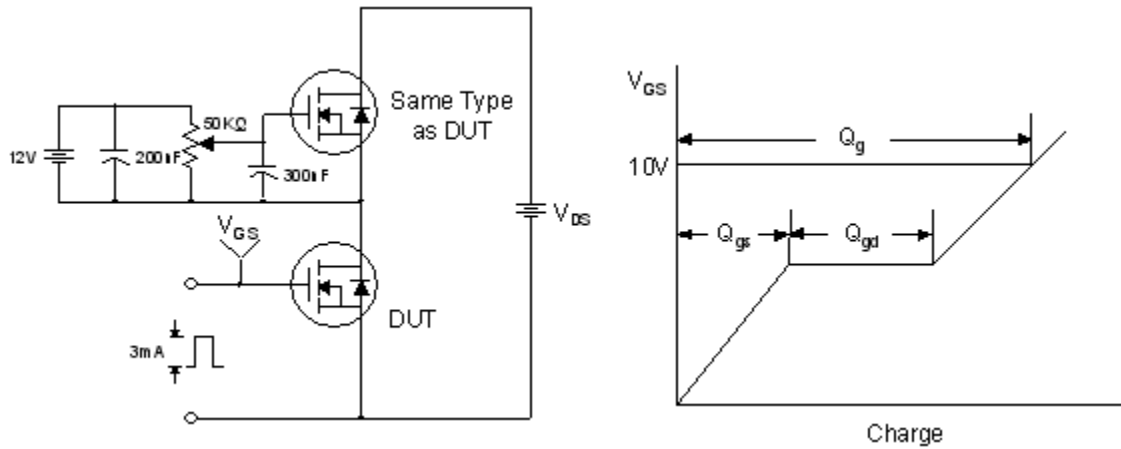
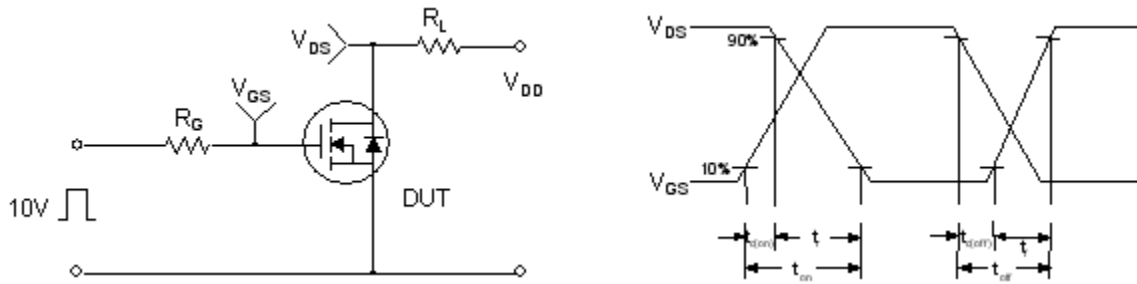


Figure 11-2. Transient Thermal Response Curve for FQPF8N90C

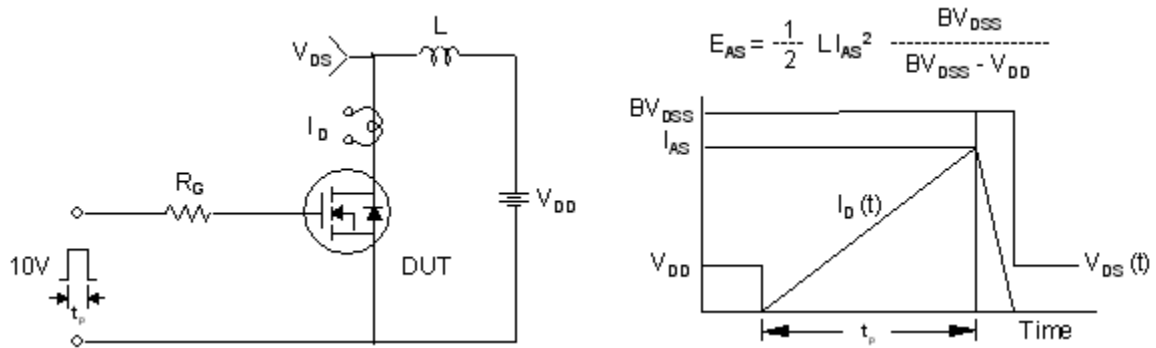
**Gate Charge Test Circuit & Waveform**



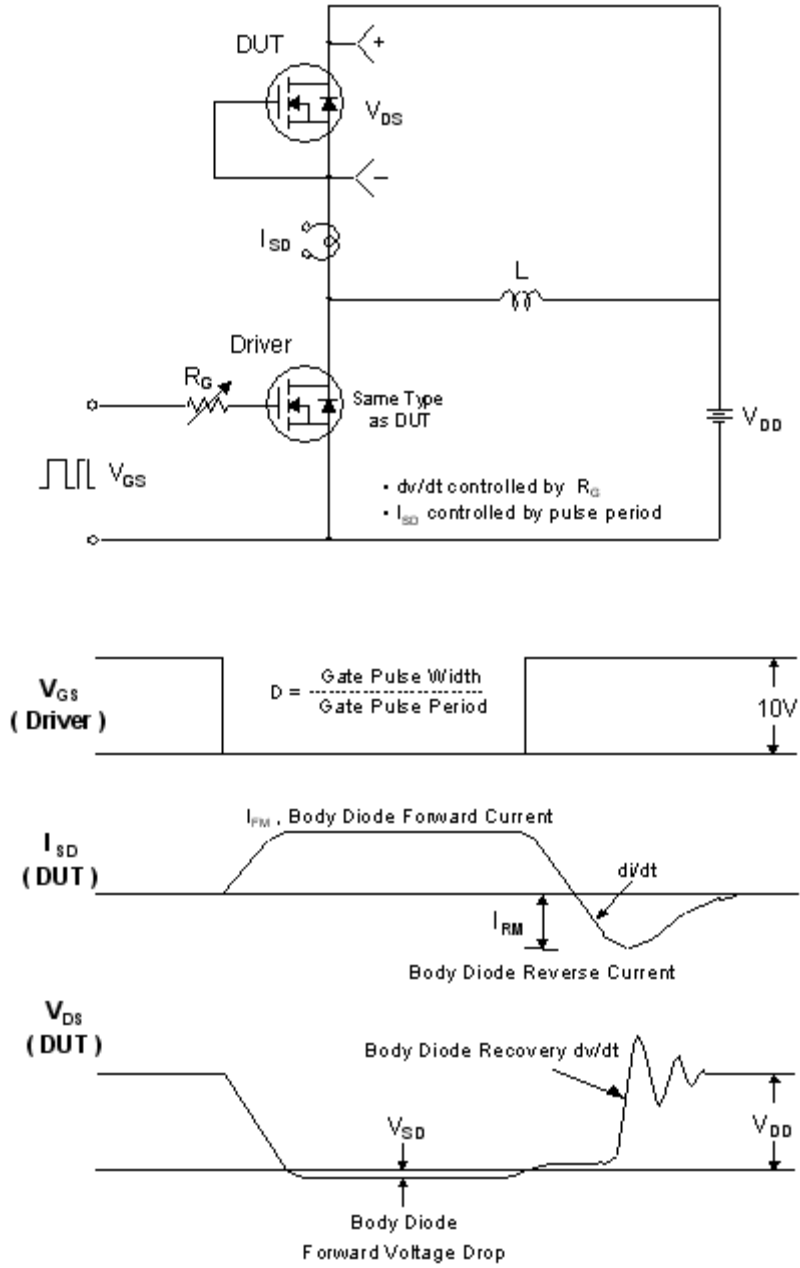
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

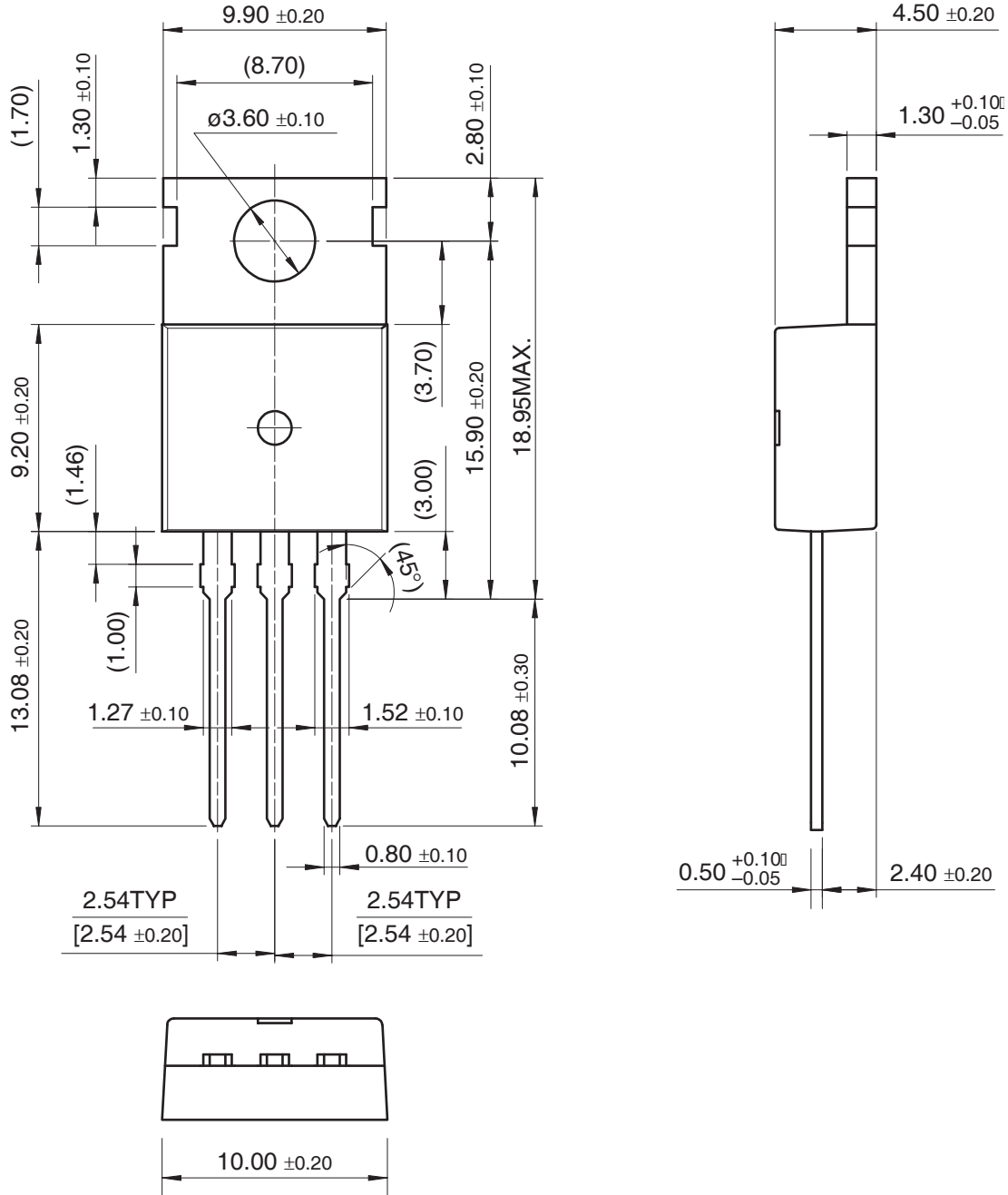


Peak Diode Recovery dv/dt Test Circuit & Waveforms



# Package Dimensions

## TO-220

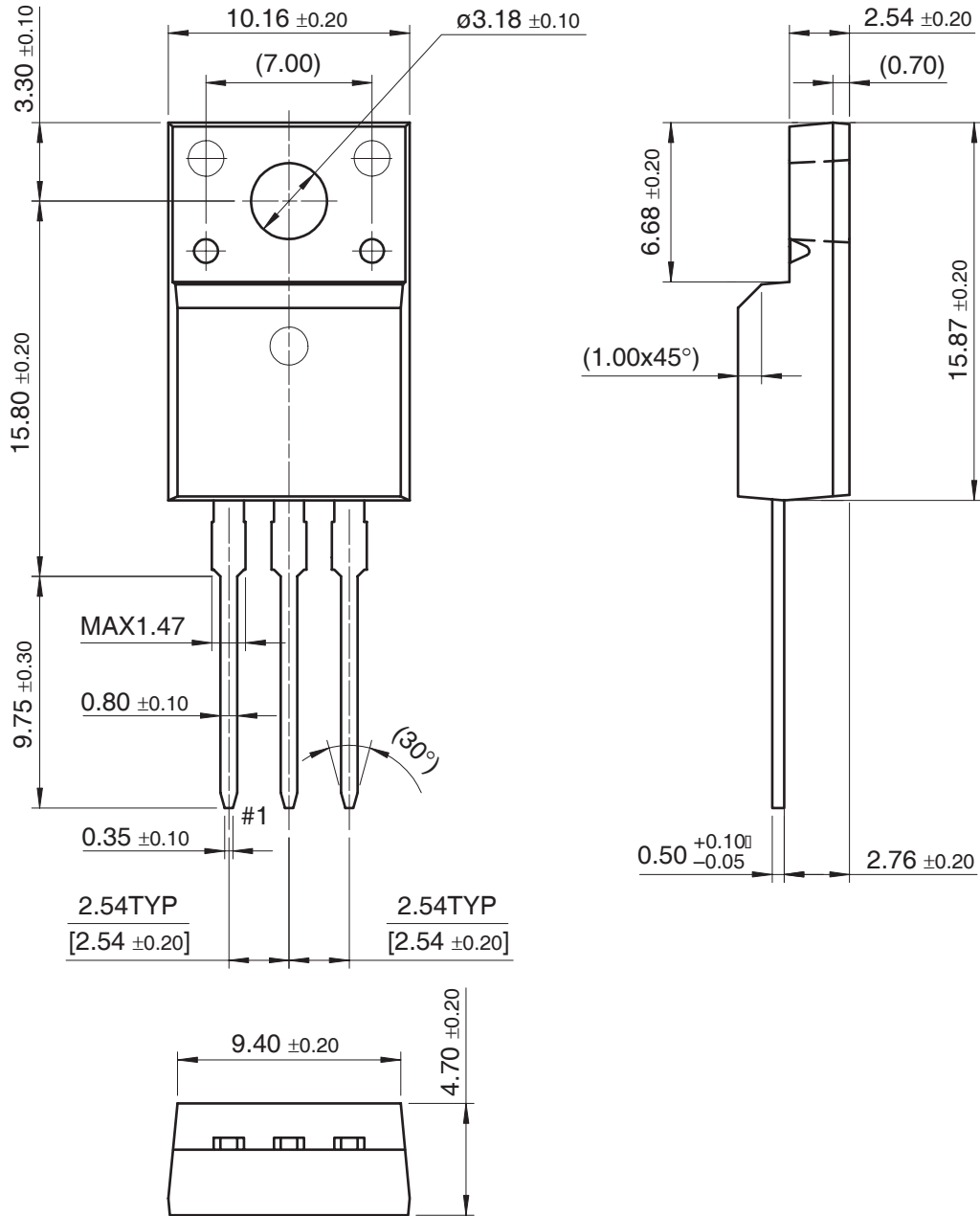


FQP8N90C/FQPF8N90C 900V N-Channel MOSFET

Dimensions in Millimeters

Package Dimensions (Continued)

TO-220F



FQP8N90C/FQPF8N90C 900V N-Channel MOSFET

Dimensions in Millimeters

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